

# Agilent ABA-53563 3.5 GHz Broadband Silicon RFIC Amplifier Data Sheet

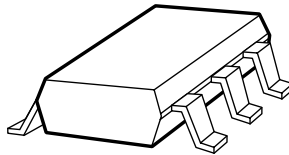
## Description

Agilent's ABA-53563 is an economical, easy-to-use, internally 50-ohm matched silicon monolithic amplifier that offers excellent gain and flat broadband response from DC to 3.5 GHz. Packaged in an ultraminiature industry-standard SOT-363 package, it requires half the board space of a SOT-143 package.

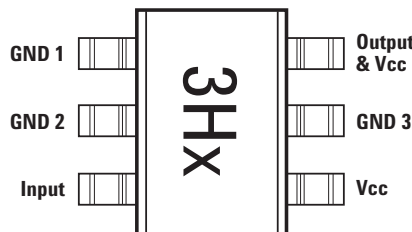
At 2 GHz, the ABA-53563 offers a small-signal gain of 21.5 dB, output P1dB of 12.7 dBm and 22.9 dBm output third order intercept point. It is suitable for use as buffer amplifiers for wideband applications. They are designed for low cost gain blocks in cellular applications, DBS tuners, LNB and other wireless communications systems.

ABA-53563 is fabricated using Agilent's HP25 silicon bipolar process, which employs a double-diffused single polysilicon process with self-aligned submicron emitter geometry. The process is capable of simultaneous high  $f_T$  and high NPN breakdown (25 GHz  $f_T$  at 6V BVCEO). The process utilizes industry standard device oxide isolation technologies and submicron aluminum multilayer interconnect to achieve superior performance, high uniformity, and proven reliability.

## Surface Mount Package SOT-363 / SC70

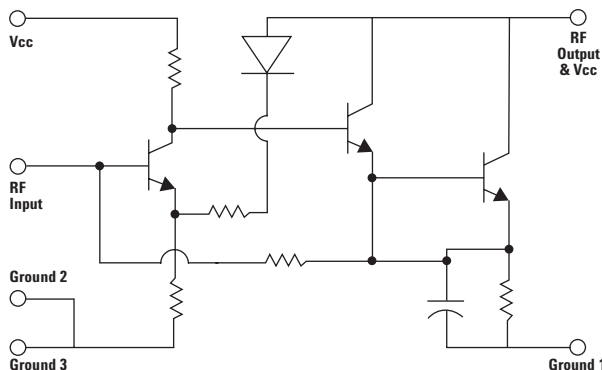


## Pin Connections and Package Marking



**Note:**  
Top View. Package marking provides orientation and identification. "x" is character to identify date code.

## Simplified Schematic



## Features

- Operating frequency: DC ~ 3.5 GHz
- 21.5 dB gain
- VSWR < 2.0 throughout operating frequency
- 12.7 dBm output P1dB
- 3.5 dB noise figure
- Unconditionally stable
- Single 5V supply ( $I_d = 46$  mA)

## Applications

- Amplifier for cellular, cordless, special mobile radio, PCS, ISM, wireless LAN, DBS, TVRO, and TV tuner applications



### ABA-53563 Absolute Maximum Ratings<sup>[1]</sup>

Symbol	Parameter	Units	Absolute Max.
$V_{cc}$	Device Voltage, RF output to ground (T = 25°C)	V	+7
$P_{in}$	CW RF Input Power (V <sub>cc</sub> = 5V)	dBm	+20
$P_{diss}$	Total Power Dissipation <sup>[3]</sup>	W	0.47
$T_j$	Junction Temperature	°C	150
$T_{STG}$	Storage Temperature	°C	-65 to 150

### Thermal Resistance<sup>[2]</sup> (V<sub>cc</sub> = 5V)

$$\theta_{jc} = 117^{\circ}\text{C}/\text{W}$$

#### Notes:

1. Operation of this device in excess of any of these limits may cause permanent damage.
2. Thermal resistance measured using 150°C Liquid Crystal Measurement Technique.
3. Board (package belly) temperature, T<sub>b</sub>, is 25°C. Derate 8.5 mW/°C for T<sub>b</sub> > 94.8°C.

### Electrical Specifications

T<sub>c</sub> = +25°C, Z<sub>0</sub> = 50 Ω, P<sub>in</sub> = -30 dBm, V<sub>cc</sub> = 5V, Freq = 2 GHz, unless stated otherwise.

Symbol	Parameter and Test Condition	Units	Min.	Typ.	Max.	Std Dev.
G <sub>p</sub> <sup>[1]</sup>	Power Gain ( $ S_{21} ^2$ )	dB	20	21.5		0.2
ΔG <sub>p</sub>	Power Gain Flatness, f = 0.1 ~ 2.5 GHz f = 0.1 ~ 3.5 GHz	dB		0.6 2.7		
NF <sup>[1]</sup>	Noise Figure	dB		3.5	4	0.11
P1dB <sup>[1]</sup>	Output Power at 1dB Gain Compression	dBm		12.7		0.14
OIP3 <sup>[1]</sup>	Output Third Order Intercept Point	dBm		22.9		0.14
VSWR <sub>in</sub> <sup>[1]</sup>	Input VSWR			1.1		
VSWR <sub>out</sub> <sup>[1]</sup>	Output VSWR			1.2		
I <sub>cc</sub> <sup>[1]</sup>	Device Current	mA		46	57	0.6
t <sub>d</sub> <sup>[1]</sup>	Group Delay	ps		160		

#### Notes:

1. Measurements taken on 50Ω test board shown on Figure 1. Excess circuit losses had been de-embedded from actual measurements. Standard deviation and typical data based on at least 500 parts sample size from 6 wafer lots. Future wafers allocated to this product may have nominal values anywhere within the upper and lower spec limits.

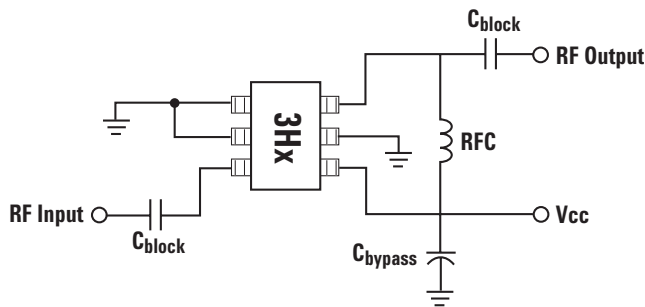


Figure 1. ABA-53563 Production Test Circuit.

## ABA-53563 Typical Performance

$T_c = +25^\circ\text{C}$ ,  $Z_o = 50\Omega$ ,  $V_{cc} = 5\text{V}$  unless stated otherwise.

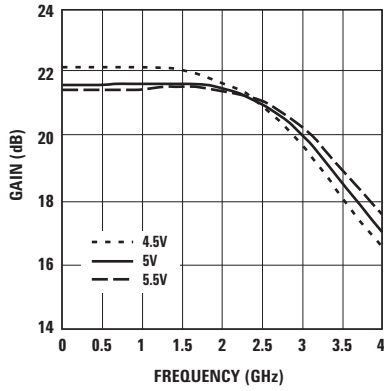


Figure 2. Gain vs. Frequency and Voltage.

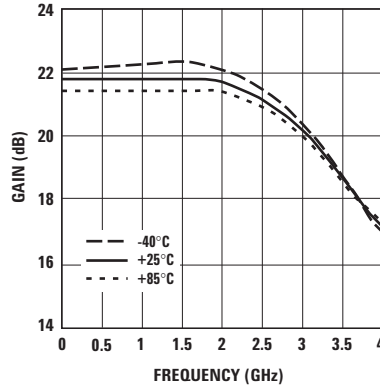


Figure 3. Gain vs. Frequency and Temperature.

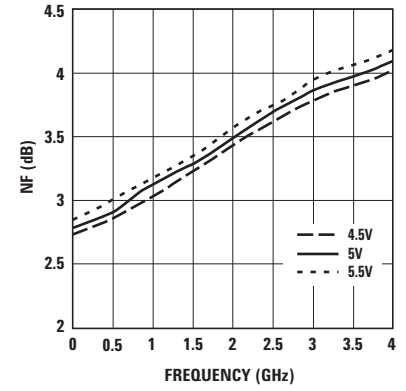


Figure 4. Noise Figure vs. Frequency and Voltage.

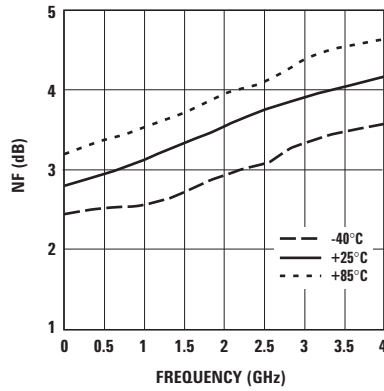


Figure 5. Noise Figure vs. Frequency and Temperature.

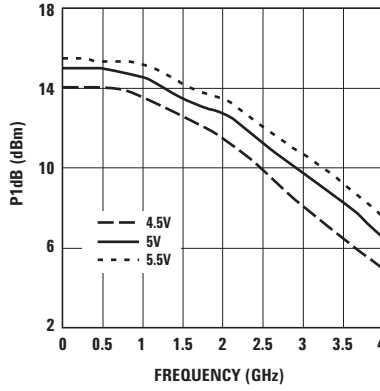


Figure 6. Output Power for 1 dB Gain Compression vs. Frequency and Voltage.

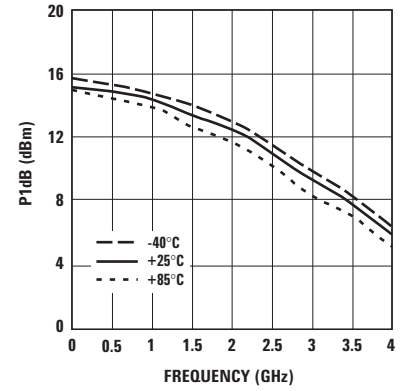
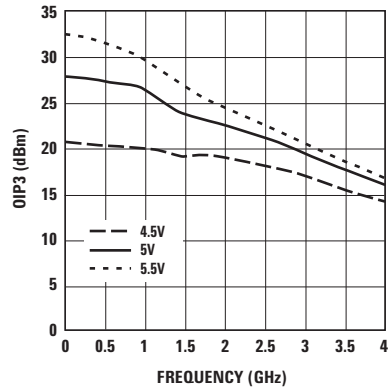


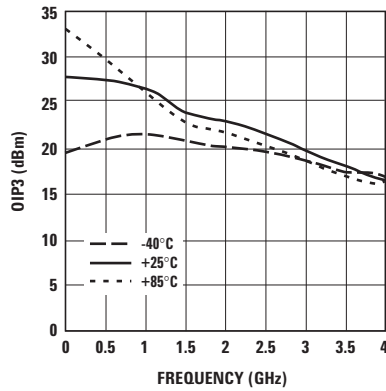
Figure 7. Output Power for 1 dB Gain Compression vs. Frequency and Temperature.

**ABA-53563 Typical Performance, continued**

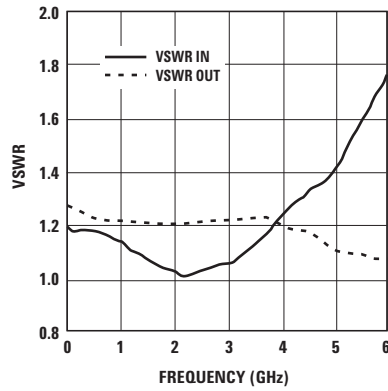
$T_c = +25^\circ\text{C}$ ,  $Z_o = 50\Omega$ ,  $V_{cc} = 5\text{V}$  unless stated otherwise.



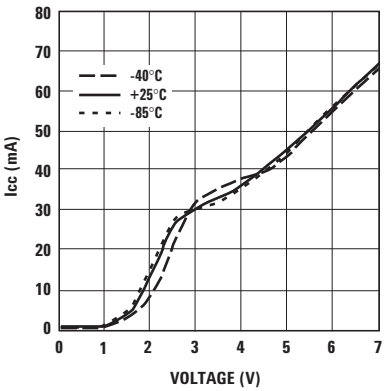
**Figure 8. Output IP3 vs. Frequency and Voltage.**



**Figure 9. Output IP3 vs. Frequency and Temperature.**



**Figure 10. Input and Output VSWR vs. Frequency.**



**Figure 11. Supply Current vs. Voltage and Temperature.**

### ABA-53563 Typical Scattering Parameters

T<sub>C</sub> = +25°C, V<sub>CC</sub> = 5V, Z<sub>0</sub> = 50 Ω, unless stated otherwise

Freq (GHz)	S <sub>11</sub> Mag.	S <sub>11</sub> Ang.	S <sub>21</sub> dB	S <sub>21</sub> Mag.	S <sub>21</sub> Ang.	S <sub>12</sub> dB	S <sub>12</sub> Mag.	S <sub>12</sub> Ang.	S <sub>22</sub> Mag.	S <sub>22</sub> Ang.	K Factor
0.05	0.09	169.3	21.6	11.98	-3.4	-29.4	0.03	-0.6	0.12	-2.3	1.414
0.10	0.08	165.6	21.5	11.87	-5.9	-29.4	0.03	-0.7	0.12	-5.8	1.424
0.20	0.08	164.9	21.5	11.85	-10.5	-29.6	0.03	-0.8	0.12	-11.7	1.458
0.30	0.08	164.3	21.5	11.85	-15.4	-29.6	0.03	-0.4	0.11	-16.5	1.458
0.40	0.08	162.9	21.5	11.86	-20.4	-29.9	0.03	0.1	0.11	-20.5	1.491
0.50	0.08	163.8	21.5	11.90	-25.5	-29.9	0.03	0.8	0.10	-23.8	1.489
0.60	0.08	162.4	21.5	11.89	-30.5	-29.9	0.03	1.7	0.10	-27.2	1.490
0.70	0.08	159.6	21.5	11.90	-35.6	-29.9	0.03	2.5	0.10	-30.9	1.490
0.80	0.08	158.1	21.5	11.92	-40.6	-29.9	0.03	3.4	0.10	-34.6	1.488
0.90	0.07	158.6	21.5	11.92	-45.7	-29.9	0.03	4.5	0.10	-36.7	1.489
1.00	0.07	158.3	21.5	11.95	-50.9	-29.9	0.03	5.5	0.10	-39.1	1.487
1.20	0.05	149.9	21.6	12.00	-61.3	-29.9	0.03	7.7	0.10	-41.7	1.483
1.40	0.04	147.4	21.6	12.04	-71.9	-29.6	0.03	9.5	0.10	-42.7	1.448
1.60	0.03	139.0	21.6	12.06	-83.0	-29.6	0.03	11.5	0.09	-43.3	1.446
1.80	0.02	127.0	21.6	12.01	-94.4	-29.4	0.03	13.0	0.09	-42.3	1.420
2.00	0.01	94.0	21.5	11.89	-105.8	-28.9	0.04	14.5	0.09	-38.8	1.374
2.20	0.01	-22.9	21.4	11.77	-117.4	-29.6	0.04	15.4	0.09	-36.3	1.356
2.40	0.01	-49.8	21.2	11.53	-129.2	-28.4	0.04	15.8	0.10	-34.4	1.348
2.60	0.02	-83.6	21.0	11.21	-141.1	-28.0	0.04	15.8	0.10	-33.9	1.327
2.80	0.03	-95.4	20.7	10.79	-153.1	-27.7	0.04	16.4	0.10	-33.7	1.338
3.00	0.03	-112.0	20.2	10.25	-164.9	-27.5	0.04	16.9	0.10	-32.1	1.362
3.20	0.04	-128.4	19.7	9.68	-176.1	-26.9	0.05	16.8	0.10	-28.9	1.348
3.40	0.06	-146.0	19.2	9.08	173.1	-26.6	0.05	16.2	0.10	-30.1	1.364
3.50	0.06	-152.9	18.9	8.78	167.7	-26.4	0.05	16.0	0.10	-30.9	1.373
4.00	0.11	170.6	17.4	7.41	143.3	-25.8	0.05	14.1	0.09	-38.3	1.477
4.50	0.14	137.6	16.0	6.30	120.2	-24.7	0.06	12.9	0.08	-41.5	1.505
5.00	0.17	122.9	14.3	5.21	99.1	-23.9	0.06	10.0	0.05	-57.3	1.612
5.50	0.23	110.6	13.0	4.47	80.1	-22.9	0.07	5.1	0.04	-82.0	1.624
6.00	0.28	99.6	11.8	3.88	63.4	-22.0	0.08	-0.2	0.04	-142.5	1.656





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